



40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max (A) T _A = +25°C
40)/	25mΩ @ V _{GS} = -10V	-8.0A
-40V	45mΩ @ V _{GS} = -4.5V	-6.0A

Features and Benefits

- Low R_{DS(ON)} Minimizes Conduction Losses
- Fast Switching Speed Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

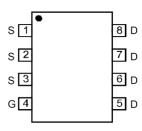
- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment

Mechanical Data

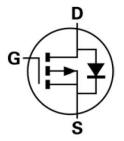
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.074 grams (Approximate)







Pin-Out Top View



Internal Schematic

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP4025LSSQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll = Manufacturer's Marking
P4025LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±20	V
		(Note 7)		-8.0	
Continuous Drain Current	V _{GS} = -10V	T _A = +70°C (Note 7)	I _D	-6.9	
		(Note 6)		-6.0	Α
Pulsed Drain Current	$V_{GS} = -10V$	(Note 8)	I _{DM}	-30	
Continuous Source Current (Body Diode)		(Note 8)	Is	-8.0	
Pulsed Source Current (Body Diode) (No		(Note 8)	I _{SM}	-30	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	Б	1.52	W	
Power Dissipation	(Note 7)	P _D	2.4		
Thermal Resistance, Junction to Ambient	(Note 6)	82			
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	52	°C/W	
Thermal Resistance, Junction to Lead (Note 9)		$R_{ heta JL}$	48.85		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV_{DSS}	-40	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1.0	μΑ	V _{DS} = -40V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	$V_{GS(TH)}$	-0.8	-1.3	-1.8	V	$I_D = -250 \mu A, V_{DS}$	= V _{GS}
Static Drain-Source On-Resistance			18	25	0	V _{GS} = -10V, I _D = -3A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	30	45	mΩ	$V_{GS} = -4.5V, I_{D} =$	-3A
Forward Transconductance	g FS		16.6	_	S	$V_{DS} = -5V, I_{D} = -3$	3A
Diode Forward Voltage	V_{SD}		-0.7	-1.0	V	I _S = -1A, V _{GS} = 0V	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{ISS}		1,640	_		$V_{DS} = -20V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		179	_	pF		
Reverse Transfer Capacitance	C _{RSS}	_	128	_			
Gate Resistance	Rg	_	6.43	_	Ω	$V_{DS} = 0V, V_{GS} =$	0V, f = 1MHz
Total Gate Charge	Q_{G}	_	14.0	_		V _{GS} = -4.5V	
Total Gate Charge	Q_{G}	_	33.7	_	nC	$V_{GS} = -10V$ $V_{DS} = -20V$ $I_{D} = -3A$	$V_{DS} = -20V$
Gate-Source Charge	Q_GS	_	5.5	_	IIC		$I_D = -3A$
Gate-Drain Charge	Q_{GD}	_	7.3	_			
Turn-On Delay Time	t _{D(ON)}	_	6.9	_		V _{DD} = -20V, V _{GS} = -10V I _D = -3A	
Turn-On Rise Time	t _R	_	14.7	_			
Turn-Off Delay Time	t _{D(OFF)}	_	53.7	_	ns		
Turn-Off Fall Time	t _F	_	30.9	_			

6. For a device surface mounted on minimum recommended FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition.

10. Short duration pulse test used to minimize self-heating effect.

^{7.} Same as Note (6), except the device is surface mounted on 25mm x 25mm x 1.6mm FR4 PCB.

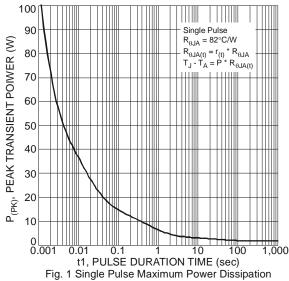
8. Repetitive rating on 25mm X 25mm FR4 PCB, D=0.02, pulse width 300µs – pulse width by maximum junction temperature.

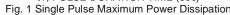
9. Thermal resistance from junction to solder-point (at the end of the drain lead).

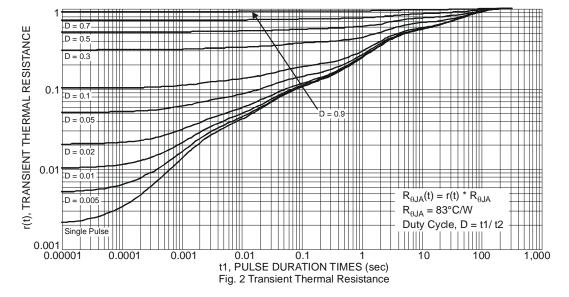
^{11.} Guaranteed by design. Not subject to production testing.



Thermal Characteristics

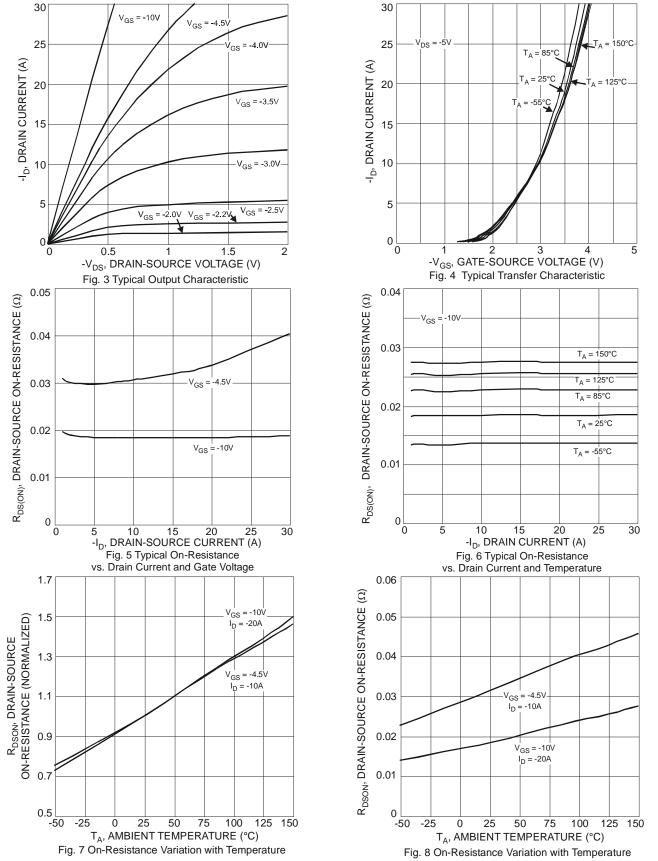




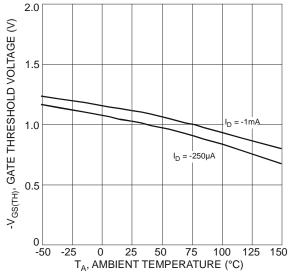


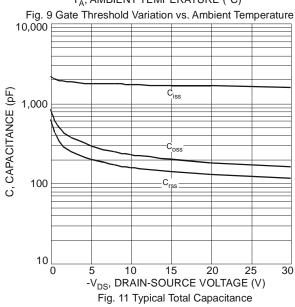


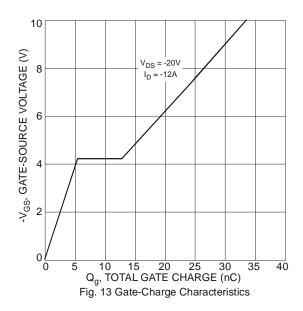
Typical Characteristics

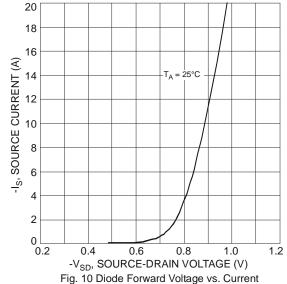


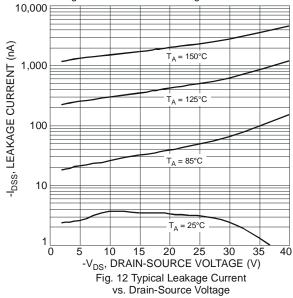










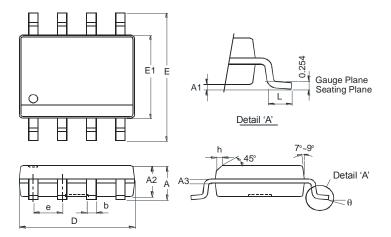




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

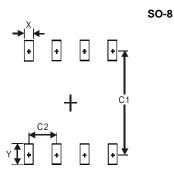
SO-8



	SO-8				
Dim	Min	Max			
Α	_	1.75			
A1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	_	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27

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